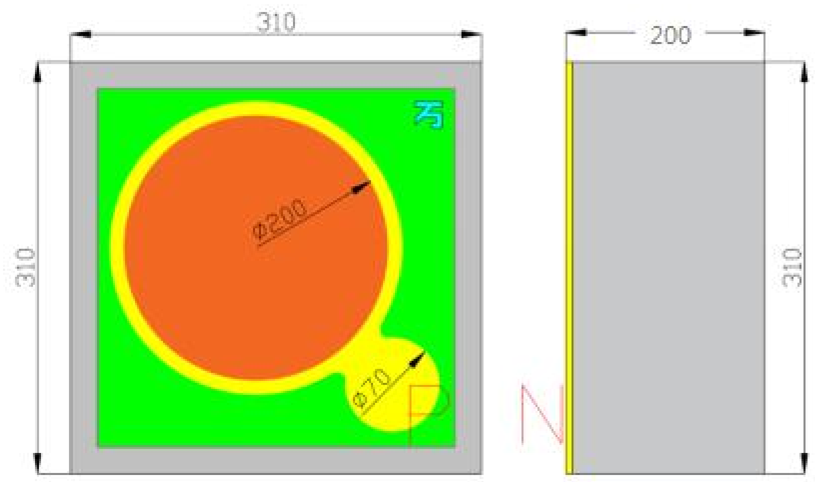
1740nm InGaAs 200um PD Chip datasheet

P/N : WIR3-01B



Feature

High responsivity
Low dark current
900-1740nm Spectral range

Structure

InGaAs / InP PIN Chip.
P Electrode (anode) : Gold.
N Electrode (cathode) : Gold.

DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active		200		µm
Chip width		310		µm
Chip length		310		µm
Chip height	180	200	220	µm
Pad Area		70		µm

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	-10V		0.3	1	nA
Responsivity	R	@1653 nm	0.9	0.95		A/W
Capacitance	Cp	f=1MHz,Vr=-3V		3	5	pF
Wavelength range	λ	-	900	1650	1740	nm

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40℃ to 85℃
Storage Temperature	-55℃ to 125℃
Forward Current	10mA